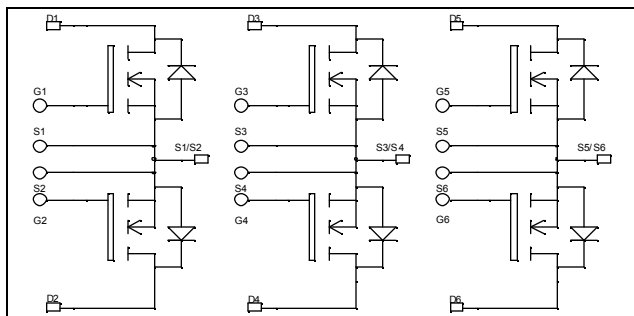


Triple dual Common Source Super Junction MOSFET Power Module

$$V_{DSS} = 600V$$

$$R_{DSon} = 35m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 72A \text{ @ } T_c = 25^\circ C$$

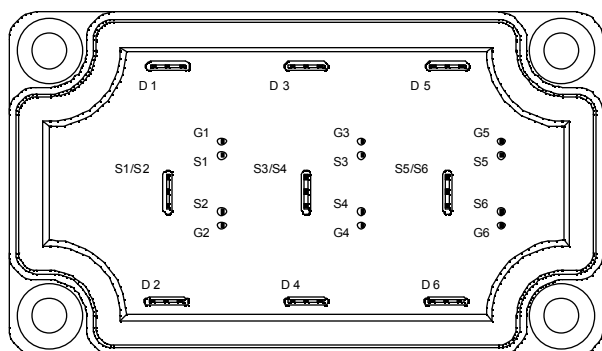


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$: 72 $T_c = 80^\circ C$: 54	A
I_{DM}	Pulsed Drain current	200	
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	35	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$: 416	W
I_{AR}	Avalanche current (repetitive and non repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy	1	mJ
E_{AS}	Single Pulse Avalanche Energy	1800	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 375\mu A$	600			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V, T_j = 25^\circ\text{C}$		1	40	μA
		$V_{GS} = 0V, V_{DS} = 600V, T_j = 125^\circ\text{C}$			375	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 72A$			35	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5.4mA$	2.1	3	3.9	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		14		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		5.13		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$		518		nC
Q_{gs}	Gate - Source Charge	$V_{Bus} = 300V$		58		
Q_{gd}	Gate - Drain Charge	$I_D = 72A$		222		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 400V$ $I_D = 72A$ $R_G = 2.5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			283		
T_f	Fall Time			84		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		1340		μJ
E_{off}	Turn-off Switching Energy ❷			1960		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		2192		μJ
E_{off}	Turn-off Switching Energy ❷			2412		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$		72		A
		$T_c = 80^\circ\text{C}$		54		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -72A$			1.2	V
dv/dt	Peak Diode Recovery ❸				6	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -72A$ $V_R = 350V$		580		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 200A/\mu s$ $T_j = 25^\circ\text{C}$		46		μC

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

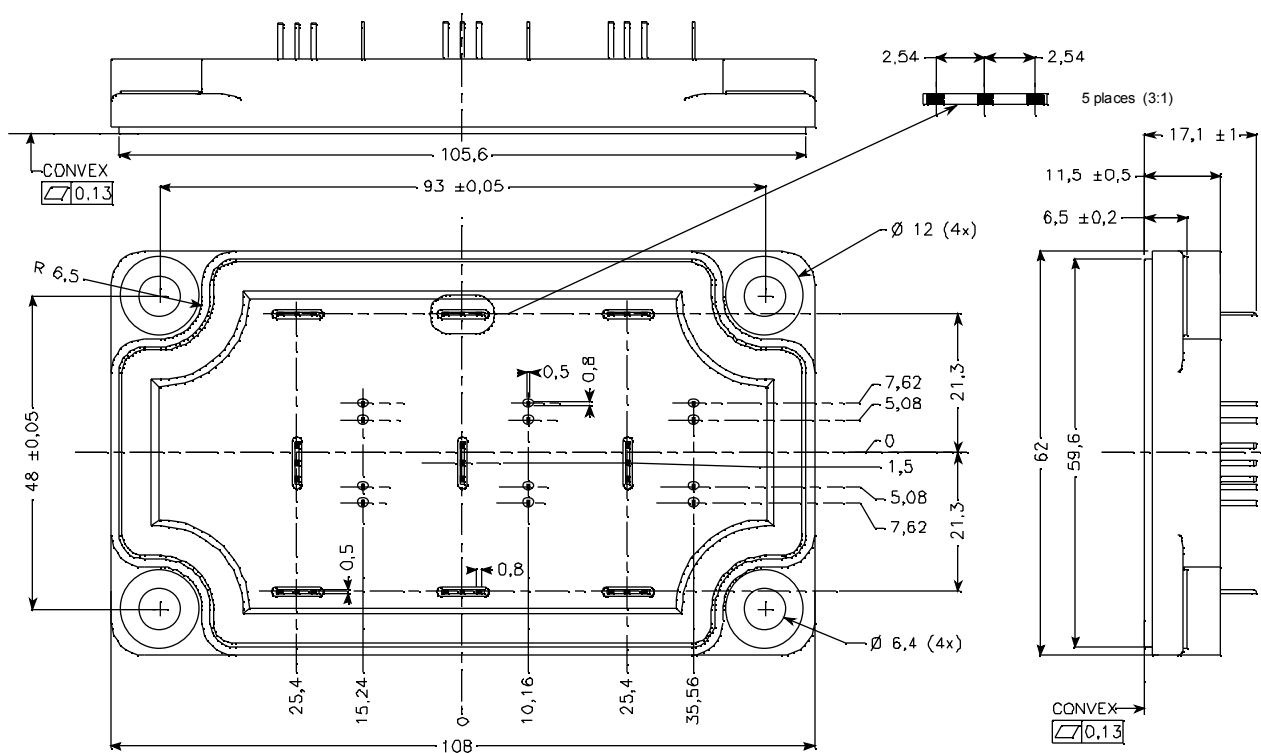
❸ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -72A \quad di/dt \leq 200A/\mu s \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

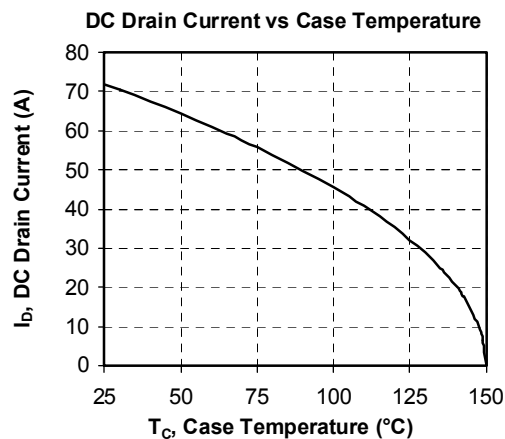
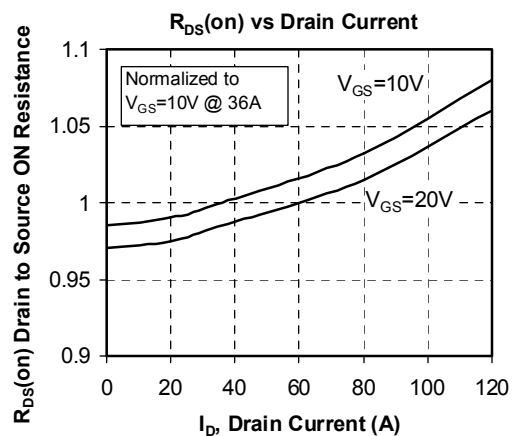
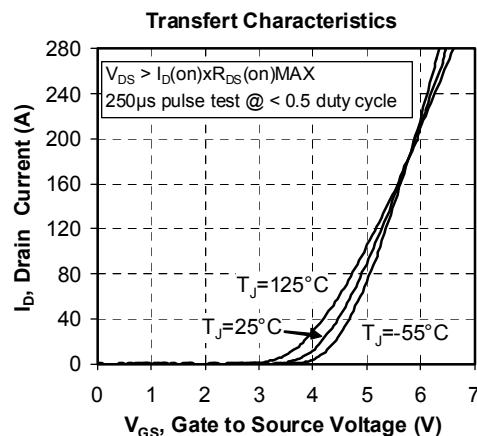
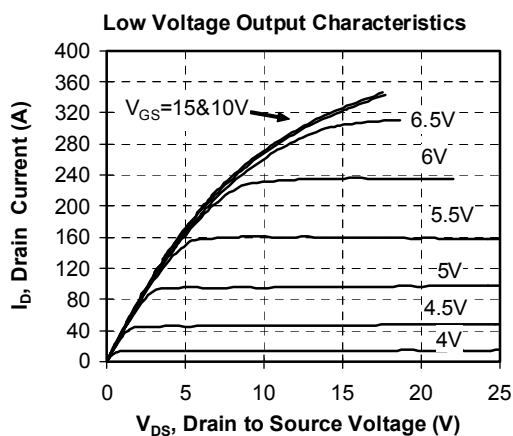
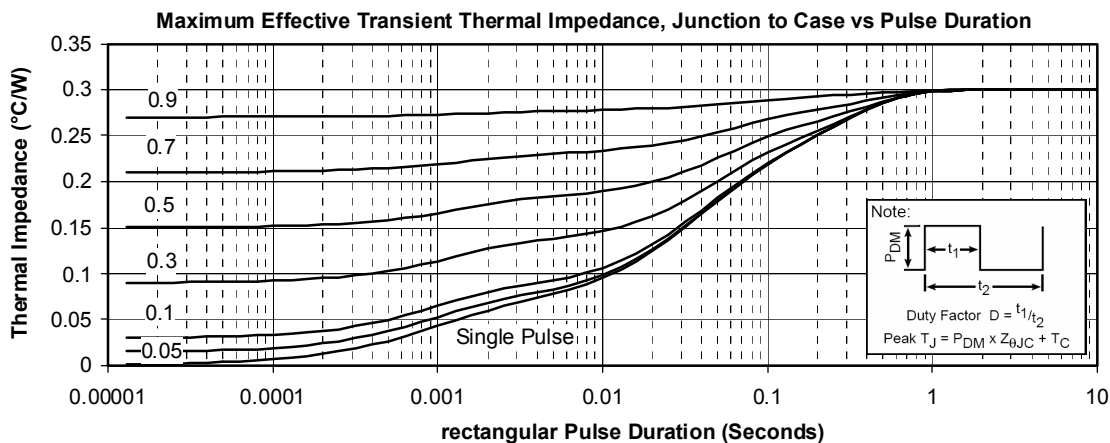
Thermal and package characteristics

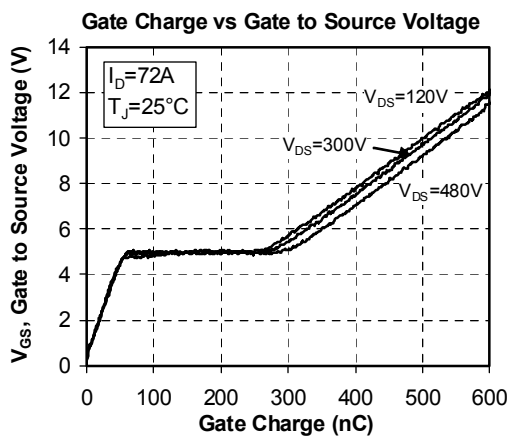
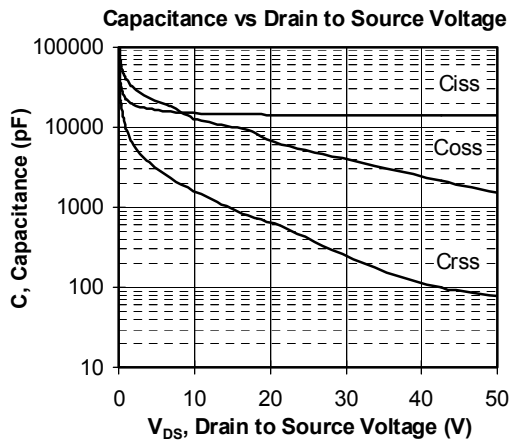
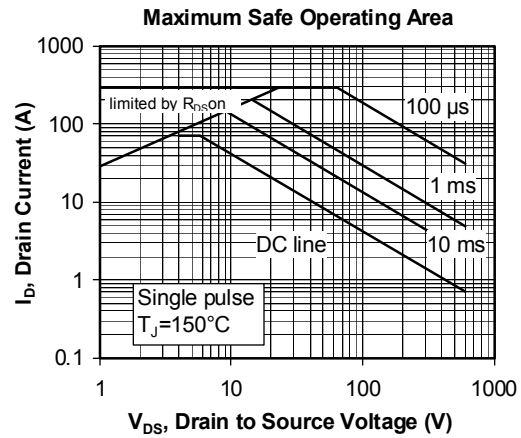
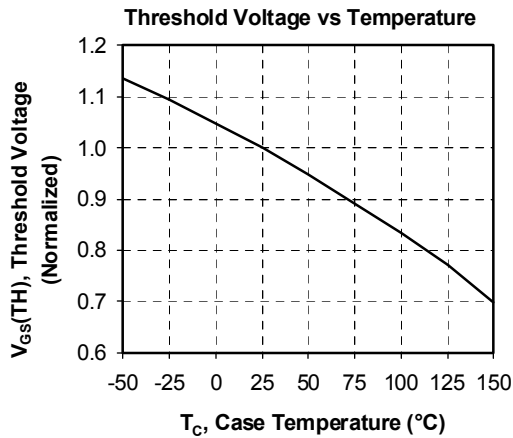
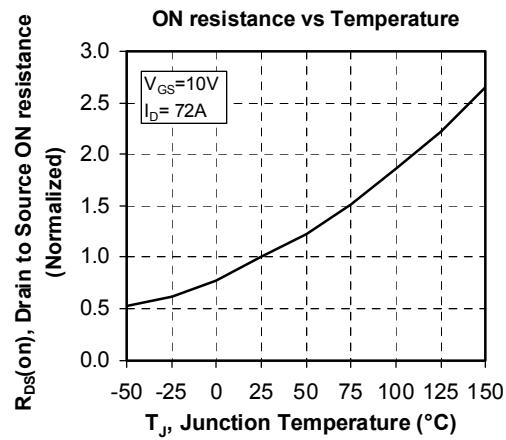
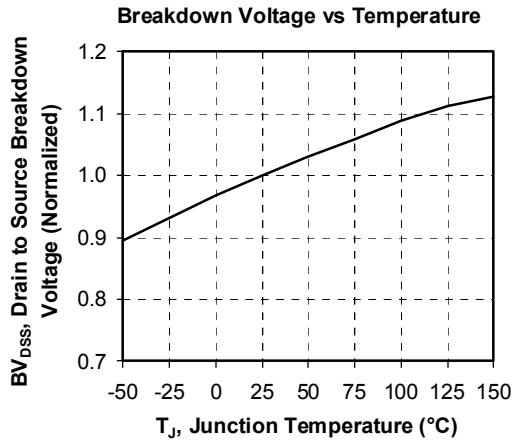
Symbol				Characteristic	Min	Typ	Max	Unit
R _{thJC}		Junction to Case					0.3	°C/W
V _{ISOL}		RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J		Operating junction temperature range			-40		150	°C
T _{STG}		Storage Temperature Range			-40		125	
T _C		Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m	
Wt	Package Weight						250	g

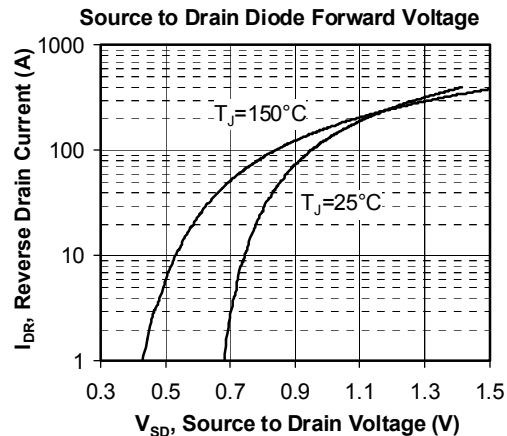
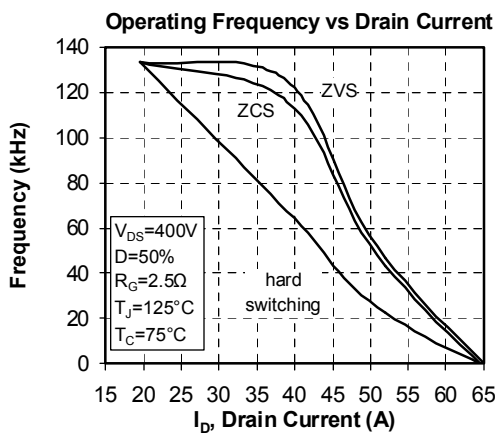
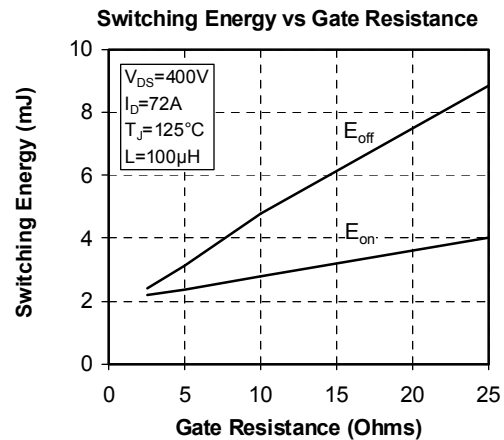
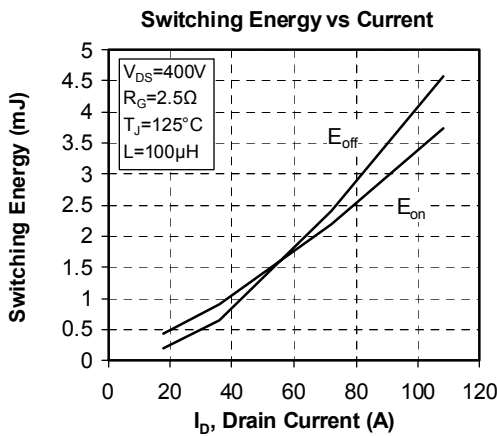
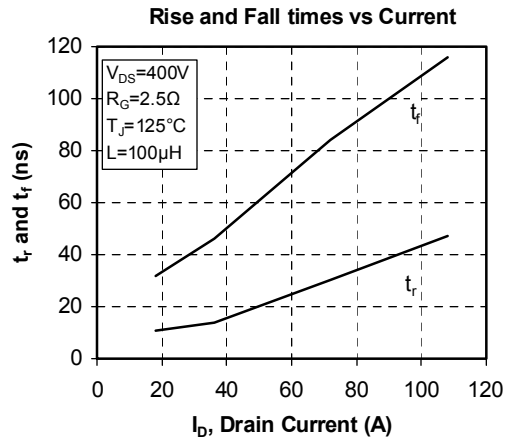
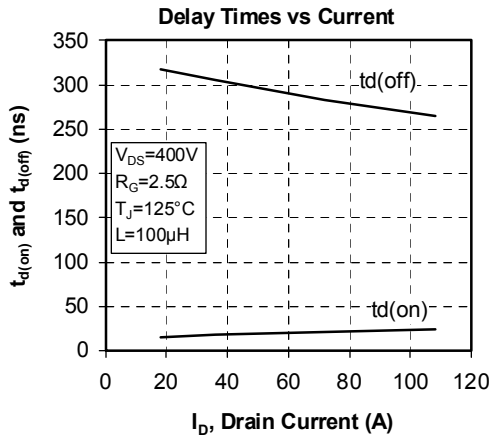
Package outline



Typical Performance Curve







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